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| Autore                  | Delpach Estelle Maryline  |
| Titolo                  | Comparable corpora and computer-assisted translation / / Estelle Maryline Delpach ; series editor, Narendra Jussien   |
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| Formato                 | Materiale a stampa  |
| Livello bibliografico   | Monografia  |
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| Nota di contenuto       | Cover; Title Page; Copyright; Contents; Acknowledgments; Introduction; PART 1: Applicative and Scientific Context; Chapter 1: Leveraging Comparable Corpora for Computer-assisted Translation ; 1.1. Introduction; 1.2. From the beginnings of machine translation to comparable corpora processing; 1.2.1. The dawn of machine translation; 1.2.2. The development of computer-assisted translation; 1.2.3. Drawbacks of parallel corpora and advantages of comparable corpora; 1.2.4. Difficulties of technical translation; 1.2.5. Industrial context<br>1.3. Term alignment from comparable corpora: a state-of-the-art<br>1.3.1. Distributional approach principle; 1.3.2. Term alignment evaluation; 1.3.2.1. Precision at rank N or TopN; 1.3.2.2. MRR; 1.3.2.3. MAP; 1.3.3. Improvement and variants of the distributional approach; 1.3.3.1. Favoring distributional symmetry; 1.3.3.2. Using syntactic contexts; 1.3.3.3. Relying on trusted elements; 1.3.3.4. Improving semantic information representation; 1.3.3.5. Using second-order semantic affinities; 1.3.3.6. Improving the bilingual resource with semantic classes; 1.3.3.7. Translating polylexical units<br>1.3.4. Influence of data and parameters on alignment quality<br>1.3.4.1. |

Data; 1.3.4.2. Parameters; 1.3.5. Limits of the distributional approach; 1.4. CAT software prototype for comparable corpora processing; 1.4.1. Implementation of a term alignment method; 1.4.1.1. Implementation and data; 1.4.1.2. Extraction of the terms to be aligned; 1.4.1.3. Collecting context vectors; 1.4.1.3.1. Monolexical term context vectors; 1.4.1.4. Polylexical term context vectors; 1.4.1.5. Translation of the source context vectors; 1.4.1.6. Term alignment; 1.4.2. Terminological records extraction  
1.4.3. Lexicon consultation interface  
1.5. Summary; Chapter 2: User-Centered Evaluation of Lexicons Extracted from Comparable Corpora; 2.1. Introduction; 2.2. Translation quality evaluation methodologies; 2.2.1. Machine translation evaluation; 2.2.1.1. Automatic evaluation measures; 2.2.1.2. Human MT evaluation; 2.2.2. Human translation evaluation; 2.2.2.1. Quantitative models; 2.2.2.2. Non-quantitative models; 2.2.3. Discussion; 2.3. Design and experimentation of a user-centered evaluation; 2.3.1. Methodological aspects; 2.3.1.1. Evaluation criteria and purpose  
2.3.1.2. Subject matter expertise  
2.3.1.3. Basis for comparison; 2.3.2. Experimentation protocol; 2.3.2.1. Data; 2.3.2.1.1. Comparable corpora and extracted lexica; 2.3.2.1.2. Texts to be translated; 2.3.2.1.3. Resources used in the translation situation; 2.3.2.1.4. Translators and judges; 2.3.2.2. Evaluation progress; 2.3.2.2.1. Translation phase; 2.3.2.2.2. Translation quality evaluation phase; 2.3.3. Results; 2.3.3.1. Lexicons usability; 2.3.3.1.1. Translation speed; 2.3.3.1.2. Use of resources; 2.3.3.1.3. Translators' impressions on the lexicons extracted from comparable corpora  
2.3.3.2. Quality of the generated translations

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#### Sommario/riassunto

Computer-assisted translation (CAT) has always used translation memories, which require the translator to have a corpus of previous translations that the CAT software can use to generate bilingual lexicons. This can be problematic when the translator does not have such a corpus, for instance, when the text belongs to an emerging field. To solve this issue, CAT research has looked into the leveraging of comparable corpora, i.e. a set of texts, in two or more languages, which deal with the same topic but are not translations of one another. This work had two primary objectives. The first is to

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| 2. Record Nr.           | UNISALENT0991003515769707536   |
| Autore                  | Vries, Jan : de  |
| Titolo                  | Die Gotter - Vorstellungen über den Kosmos - Der Untergang des Heidentums / von Jan de Vries   |
| Pubbl/distr/stampa      | Berlin : Walter de Gruyter, 1970   |
| Edizione                | [3., unveränderte Auflage]   |
| Descrizione fisica      | 492 p. ; 23 cm   |
| Collana                 | Altgermanische Religionsgeschichte ; 2   |
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| Lingua di pubblicazione | Tedesco  |
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| Livello bibliografico   | Monografia   |
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| 3. Record Nr.           | UNINA9910830878003321  |
| Autore                  | Enz Christian  |
| Titolo                  | Charge-based MOS transistor modeling [[electronic resource]] : the EKV model for low-power and RF IC design / Christian C. Enz, Eric A. Vittoz |
| Pubbl/distr/stampa      | Chichester, England ; ; Hoboken, NJ, : John Wiley, c2006   |
| ISBN                    | 1-280-64993-3<br>9786610649938<br>0-470-85546-0<br>0-470-85545-2   |
| Descrizione fisica      | 1 online resource (329 p.)   |
| Altri autori (Persone)  | VittozEric A. <1938->  |
| Disciplina              | 621.3815284  |
| Soggetti                | Metal oxide semiconductors - Mathematical models<br>Metal oxide semiconductor field-effect transistors - Mathematical models                   |
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## Nota di contenuto

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7.2 Temperature Effects

## Sommario/riassunto

Modern, large-scale analog integrated circuits (ICs) are essentially composed of metal-oxide semiconductor (MOS) transistors and their interconnections. As technology scales down to deep sub-micron dimensions and supply voltage decreases to reduce power consumption, these complex analog circuits are even more dependent on the exact behavior of each transistor. High-performance analog circuit design requires a very detailed model of the transistor, describing accurately its static and dynamic behaviors, its noise and matching limitations and its temperature variations. The charge-based EKV (Enz